BGU7051

SiGe:C low noise high linearity amplifier Rev. 2 — 11 November 2011

Product data sheet

Product profile 1.

1.1 General description

The BGU7051 is a low noise high linearity amplifier for wireless infrastructure applications. The LNA has a high input and output return loss and is designed to operate between 0.5 GHz and 1.5 GHz. It is housed in a $3 \times 3 \times 0.85$ mm³ 10-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

1.2 Features and benefits

- Low Noise Figure (NF) = 0.65 dB at 900 MHz
- High linearity performance, IP3_O = 33 dBm at 900 MHz
- High input and output return loss
- Unconditionally stable
- 110 GHz transit frequency SiGe:C technology
- Supply voltage 3.3 V
- Small 10-terminal leadless package 3 × 3 × 0.85 mm³
- ESD protection on all terminals
- Moisture sensitivity level 1

1.3 Applications

- LNA for wireless infrastructure applications (0.5 GHz to 1.5 GHz)
- Low noise applications

1.4 Quick reference data

Quick reference data

f = 900 MHz; V_{CC} = 3.3 V; T_{amb} = 25 °C; input and output 50 Ω; unless otherwise specified.

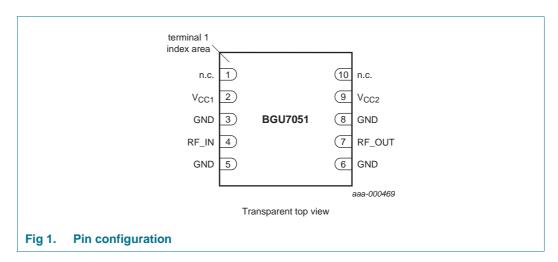
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		3.0	-	3.6	V
I _{CC}	supply current		50	65	80	mΑ
G _{ass}	associated gain		19.5	21.0	22.5	dB
NF	noise figure		-	0.65	0.95	dB
P _{L(1dB)}	output power at 1 dB gain compression		15	16.5	-	dBm
IP3 _O	output third-order intercept point		30	33	-	dBm



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2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
n.c.	1, 10	not connected
V _{CC1}	2	supply voltage
GND	3, 5, 6, 8	ground
RF_IN	4	RF input
RF_OUT	7	RF output
V _{CC2}	9	supply voltage

3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BGU7051	HVSON10	plastic thermal enhanced very thin small outline package; no leads; 10 terminals; body $3\times3\times0.85$ mm	SOT650-1			

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0	5	V
$P_{i(RF)CW}$	continuous waveform RF input power	$V_{CC} = 3.3 \text{ V}$	-	20	dBm
T_{stg}	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C
T_{amb}	ambient temperature		-40	85	°C
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	-	4	kV
		Charged Device Model (CDM); According JEDEC standard 22-C101B	-	2	kV

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		26	K/W

6. Characteristics

Table 6. Characteristics

 V_{CC} = 3.3 V; T_{amb} = 25 °C; input and output 50 Ω ; unless otherwise specified. All RF parameters are measured at the device RF in and RF output terminals.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		3.0	-	3.6	V
I _{CC}	supply current		50	65	80	mΑ
G _{ass}	associated gain	f = 750 MHz	-	23.5	-	dB
		f = 850 MHz	-	21.5	-	dB
		f = 900 MHz	19.5	21.0	22.5	dB
NF	noise figure	f = 750 MHz	-	0.6	-	dB
		f = 850 MHz	-	0.63	-	dB
		f = 900 MHz	-	0.65	0.95	dB
P _{L(1dB)}	output power at 1 dB gain compression	f = 750 MHz	-	17.0	-	dBm
		f = 850 MHz	-	16.5	-	dBm
		f = 900 MHz	15	16.5	-	dBm
IP3 _O	output third-order intercept point	2-tone; spacing 5 MHz; P _i = −20 dBm				
		f = 750 MHz	-	32	-	dBm
		f = 850 MHz	-	32	-	dBm
		f = 900 MHz	30	33	-	dBm

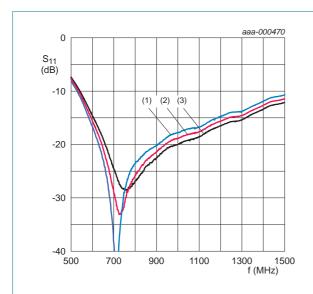
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 Table 6.
 Characteristics ... continued

 V_{CC} = 3.3 V; T_{amb} = 25 °C; input and output 50 Ω ; unless otherwise specified. All RF parameters are measured at the device RF in and RF output terminals.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
RL _{in}	input return loss	f = 750 MHz	-	27.5	-	dB
		f = 850 MHz	-	26.0	-	dB
		f = 900 MHz	-	24.5	-	dB
RL _{out}	output return loss	f = 750 MHz	-	18.0	-	dB
		f = 850 MHz	-	17.5	-	dB
		f = 900 MHz	-	18	-	dB
ISL	isolation	f = 750 MHz	-	29.5	-	dB
		f = 850 MHz	-	27.5	-	dB
		f = 900 MHz	-	26.5	-	dB
K	Rollett stability factor	$0 \text{ GHz} \le f \le 25 \text{ GHz}$	1	-	-	

6.1 Performance curves



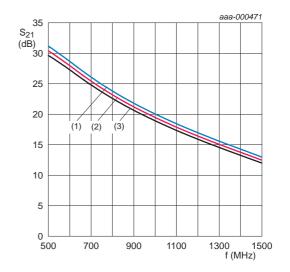
 $V_{CC} = 3.3 \text{ V}.$

(1) $T_j = -40 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

(3) $T_i = 85 \, ^{\circ}C$

Fig 2. Input reflection coefficient as a function of frequency



 $V_{CC} = 3.3 \text{ V}.$

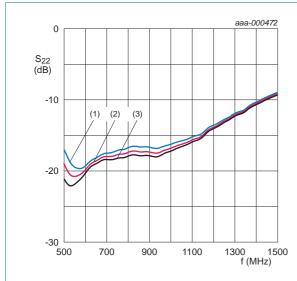
(1) $T_j = -40 \, ^{\circ}C$

(2) $T_j = 25 \, ^{\circ}C$

(3) $T_j = 85 \, ^{\circ}C$

Fig 3. Forward transmission coefficient as a function of frequency

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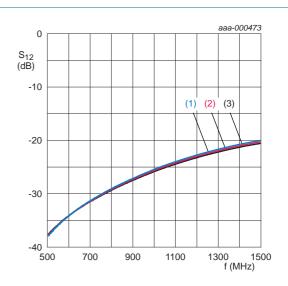
 $V_{CC} = 3.3 \text{ V}.$

(1)
$$T_i = -40 \, ^{\circ}\text{C}$$

(2)
$$T_j = 25 \, ^{\circ}C$$

(3) $T_j = 85 \, ^{\circ}C$

Fig 4. Output reflection coefficient as a function of frequency



 $V_{CC} = 3.3 \text{ V}.$

(1)
$$T_i = -40 \, ^{\circ}\text{C}$$

(2)
$$T_j = 25$$
 °C

(3) $T_j = 85 \, ^{\circ}C$

Fig 5. Reverse transmission coefficient as a function of frequency

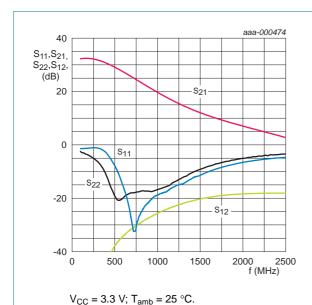
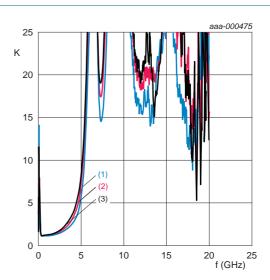


Fig 6. Wideband s-parameters as a function of frequency



 $V_{CC} = 3.3 \text{ V}.$

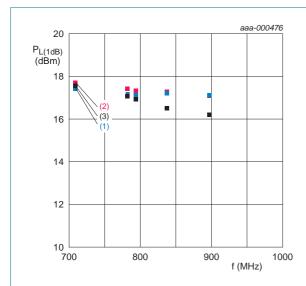
(1)
$$T_j = -40 \, ^{\circ}C$$

(2)
$$T_j = 25 \, ^{\circ}C$$

(3) $T_j = 85 \, ^{\circ}C$

Fig 7. Stability K-factor as a function of frequency

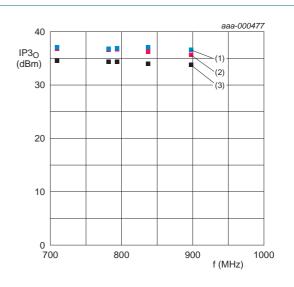
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 $V_{CC} = 3.3 \text{ V}.$

- (1) $T_i = -40 \, ^{\circ}\text{C}$
- (2) $T_j = 25 \, ^{\circ}C$
- (3) $T_j = 85 \, ^{\circ}C$

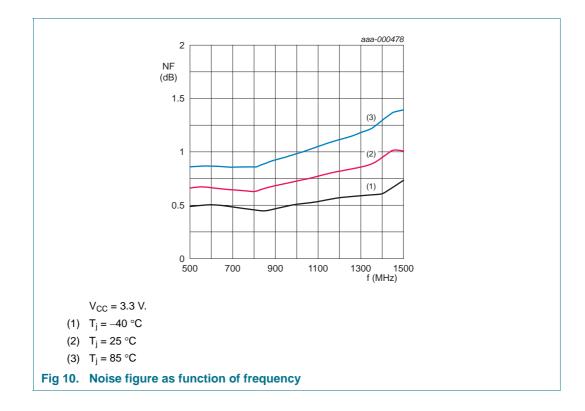
Fig 8. Output power at 1 dB gain compression as a function of frequency



 $V_{CC} = 3.3 \text{ V}.$

- (1) $T_i = -40 \, ^{\circ}\text{C}$
- (2) $T_j = 25$ °C
- (3) $T_j = 85 \, ^{\circ}C$

Fig 9. Output third-order intercept point as a function of frequency

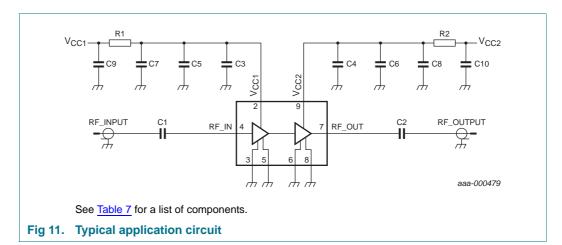


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7. Application information

<u>Figure 11</u> shows the typical application circuit for the BGU7051. The device is internally matched to 50 Ω , and therefore does not need any external matching. The value of the input and output DC blocking C1 and C2 are recommended to be 1 nF. DC decoupling capacitors C3 and C4 should be located as close as possible to the BGU7051.

In case different system blocks are supplied via the same voltage rail, it is recommended to use a bias choke in the bias line on the positions of R1 and R2. The value of this choke is depending on the frequency that needs to be decoupled.



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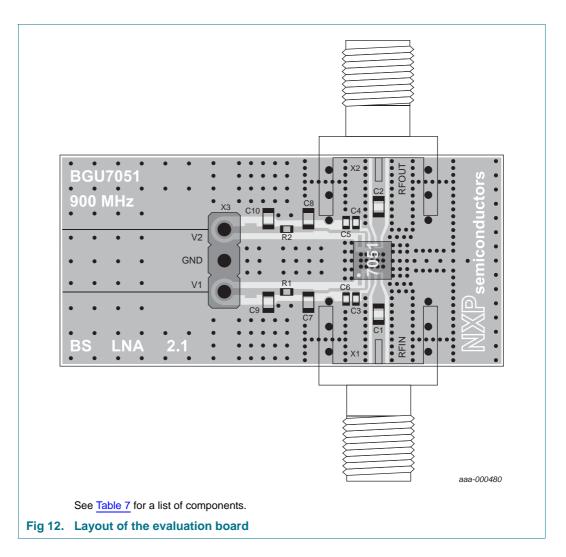


Table 7. List of components See *Figure* 11 for schematics.

Component	Description		Value	Size	Function
C1, C2	capacitor	[1]	1 nF	0402	DC block
C3, C4	capacitor	[1]	100 pF	0402	bias decoupling
C5, C6	capacitor	[1]	100 nF	0402	bias decoupling
C7, C8, C9, C10	capacitor	[2]	100 nF	0603	optional
R1, R2	resistor		0 Ω	0402	

^[1] Murata GRM155 or capacitor of same quality.

^[2] Murata GRM188 or capacitor of same quality.

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8. Package outline

HVSON10: plastic thermal enhanced very thin small outline package; no leads; 10 terminals; body $3 \times 3 \times 0.85$ mm

SOT650-1

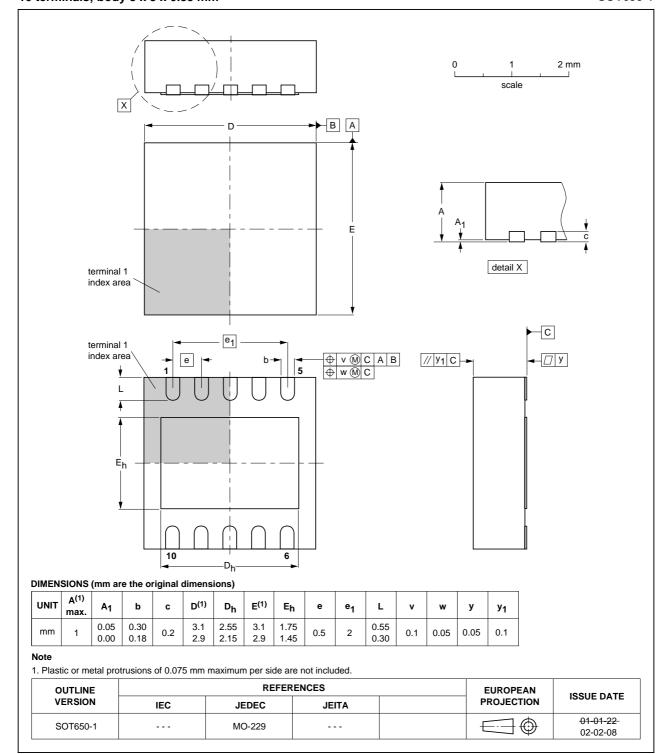


Fig 13. Package outline SOT650-1 (HVSON10)

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9. Abbreviations

Table 8. Abbreviations

Acronym	Description
AC	Alternating Current
CW	Continuous Wave
ESD	ElectroStatic Discharge
ESR	Equivalent Series Resistance
НВМ	Human Body Model
LNA	Low Noise Amplifier
PDA	Personal Digital Assistant
RF	Radio Frequency
SiGe:C	Silicon Germanium Carbon

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU7051 v.2	20111111	Product data sheet	-	BGU7051 v.1
Modifications:	Modifications: • Figure 10: data plots updated • Unit dB changed to dBm for P _{L(1dB)} in Section 6 "Characteristics"			
BGU7051 v.1	20111027	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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